RF2371

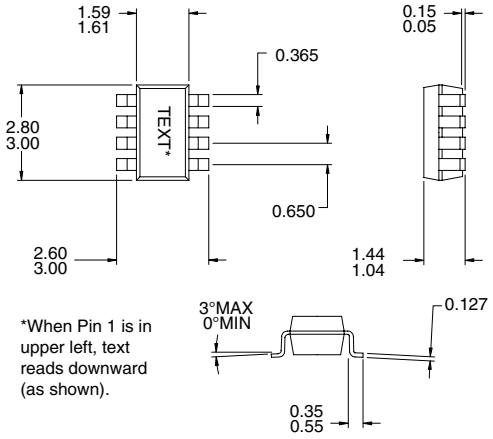
3V LOW NOISE AMPLIFIER

Typical Applications

- GSM Handsets
- CDMA Handsets
- TDMA Handsets
- IF or RF Buffer Amplifiers
- Driver Stage for Power Amplifiers
- Oscillator Loop Amplifiers

Product Description

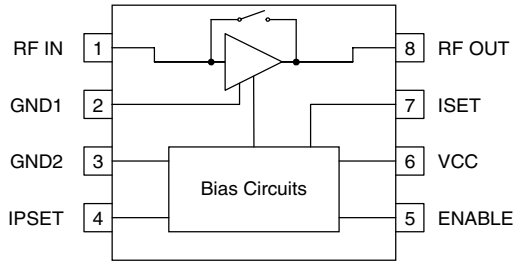
The RF2371 is a general purpose, low-cost, high performance low noise amplifier designed for operation from a 2.7V to 4V supply with low current consumption. The attenuation of the device is controlled when in power down mode, providing a known gain step. The RF2371 is available in a small industry-standard SOT23-8 surface mount package, enabling compact designs which conserve board space. The design features a highly accurate PTAT (Proportional To Absolute Temperature) biasing scheme using bandgap cells.



Package Style: SOT23-8

Optimum Technology Matching® Applied

- ☐ Si BJT
- ☑ Si Bi-CMOS
- ☐ GaAs HBT
- ☐ SiGe HBT
- ☐ GaAs MESFET
- ☐ Si CMOS



Functional Block Diagram

Features

- 700MHz to 2000MHz Operation
- 2.7V to 3.6V Single Supply
- +5dBm Input IP_3 at 3.0mA
- 12dB Gain at 1950MHz
- 1.8dB Noise Figure at 1950MHz
- 17dB Gain Step

Ordering Information

RF2371	3V Low Noise Amplifier
RF2371 PCBA	Fully Assembled Evaluation Board

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Absolute Maximum Ratings

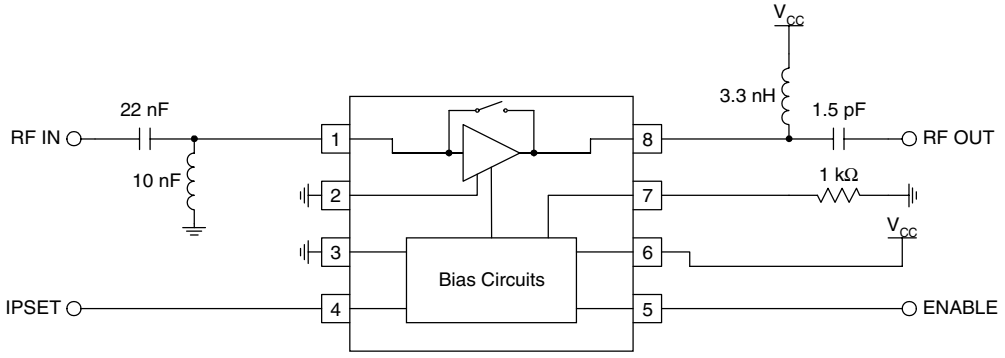
Parameter	Rating	Unit
Supply Voltage	4.0	V
Supply Current	20	mA
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-40 to +150	°C

Caution! ESD sensitive device.

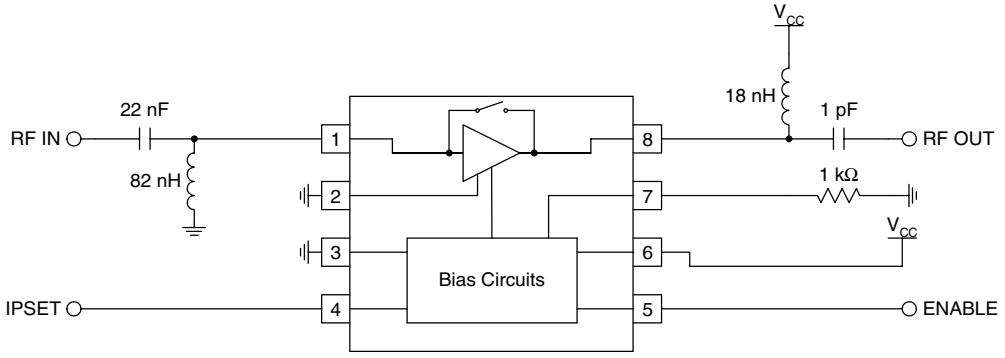
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall					T=27°C, V_{CC}=2.7V, $V_{ISELECT}$=0V, V_{ENABLE}=2.7V
Frequency Range		700 to 2000		MHz	
LNA Performance					Freq=1.95GHz
Gain	10.5	12.5		dB	
Noise Figure		1.6		dB	
Input IP3	+4.5	+8		dBm	At 2.9mA
Input VSWR		5:1		dB	(Noise match)
Output VSWR			1.5:1	dB	
Off Mode Gain		-5.0		dB	V_{ENABLE}=0V
Gain		17		dB	Freq=836MHz
Noise Figure		1.6		dB	
Input IP3		0		dBm	
Off Mode Gain		-8		dB	V_{ENABLE}=0V
Current Control					
Internal Current Setting “ON”		CMOS Low		V	Voltage on ISELECT
External Current Setting “ON”		CMOS High		V	Voltage on ISELECT
Current into ISELECT			1	µA	$V_{ISELECT}$=2.7V
Power Control					
Power “ON” Voltage		CMOS High		V	Voltage on ENABLE
Power “OFF” Voltage		CMOS Low		V	Voltage on ENABLE
Current into ENABLE			1	µA	V_{ENABLE}=2.7V
Power Supply					
Operating Voltage		2.7 to 3.6		V	
Operating Current		2.9	5	mA	V_{CC}=2.7V, Internal current setting
Leakage Current			1	µA	V_{ENABLE}=0V

Pin	Function	Description	Interface Schematic
1	RF IN	RF input pin. This pin is not internally DC blocked and requires an external blocking capacitor.	
2	GND1	Ground connection for the LNA. Keep traces physically short and connect immediately to ground plane for best performance.	
3	GND2	Ground connection for the bias circuits.	
4	IPSET	This pin selects the internal current setting when CMOS level “low”, and the external current setting when this pin is CMOS level “high”. The current is set to 2.8mA using the internal current setting, and can be up to 20mA using the external current setting.	
5	ENABLE	Power down control. This is a CMOS input. When this pin is CMOS “high” the device is enabled. When the level is CMOS “low” the device is shut off and a controlled attenuator is turned on.	
6	VCC	Power supply for the bias circuits.	
7	ISET	This pin sets the current for the device. A resistor to ground of 1kΩ provides a current of 17.5mA. The condition for optimal IP3 is to use the internal current setting option and leave this pin open (no connect).	
8	RF OUT	RF output pin. Bias for the LNA is provided through this pin, hence it should be connected to VCC through an inductor.	

Application Schematic 1.95GHz

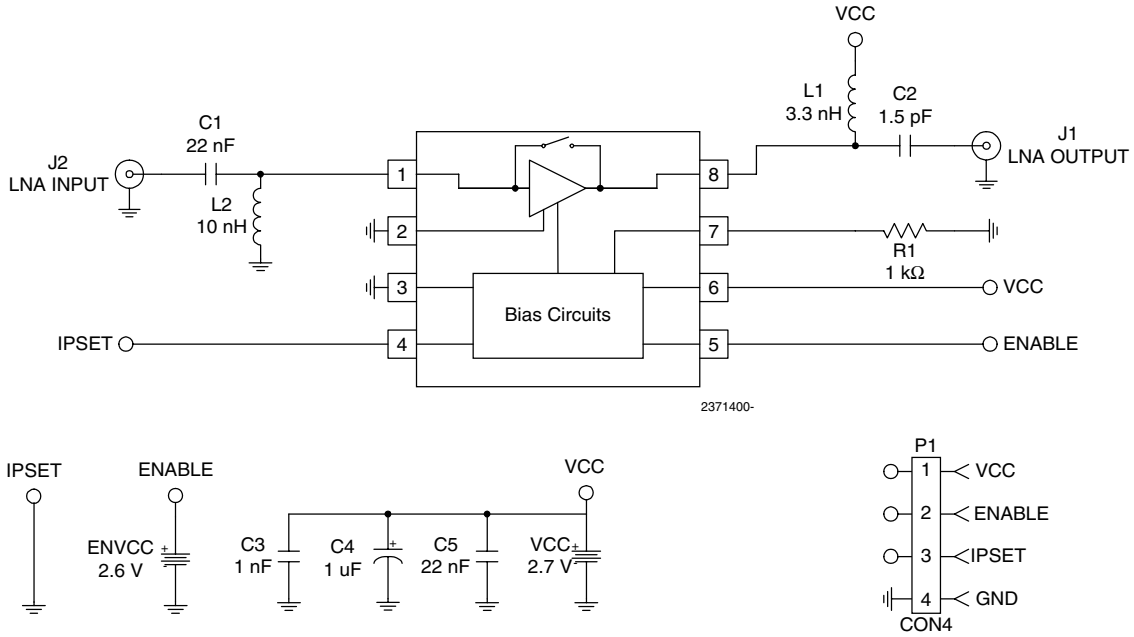


Application Schematic 836MHz



Evaluation Board Schematic

(Download Bill of Materials from www.rfmd.com.)



Evaluation Board Layout
Board Size 0.833” x 1.009”

Board Thickness 0.031”, Board Material FR-4